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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f410rbt6

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3 Functional overview

3.1 ARM® Cortex®-M4 with FPU core with embedded Flash and SRAM

The ARM® Cortex®-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM® Cortex®-M4 with FPU 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices. The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution. Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F410x8/B devices are compatible with all ARM tools and software.

Figure 2 shows the general block diagram of the STM32F410x8/B.

Note: Cortex®-M4 with FPU is binary compatible with Cortex®-M3.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM® Cortex®-M4 with FPU processors. It balances the inherent performance advantage of the ARM® Cortex®-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 125 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART Accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 100 MHz.

3.3 Batch Acquisition mode (BAM)

The Batch acquisition mode allows enhanced power efficiency during data batching. It enables data acquisition through any communication peripherals directly to memory using the DMA in reduced power consumption as well as data processing while the rest of the system is in low-power mode (including the flash and ART). For example in an audio system, a smart combination of PDM audio sample acquisition and processing from the I2S directly to RAM (flash and ART™ stopped) with the DMA using BAM followed by some very short processing from flash allows to drastically reduce the power consumption of the application. A dedicated application note (AN4515) describes how to implement the STM32F410x8/B BAM to allow the best power efficiency.

3.20.4 Low-power timer (LPTIM1)

The devices embed one low-power timer. This timer features an independent clock and runs in Stop mode if it is clocked by LSE, LSI or by an external clock. It is able to wake up the system from Stop mode.

The low-power timer main features are the following:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous/ one shot mode
- Selectable software/hardware input trigger
- Selectable clock source
  - Internal clock sources: LSE, LSI, HSI or APB1 clock
  - External clock source over LPTIM input (working even when no internal clock source is running and used by pulse-counter applications).
- Programmable digital glitch filter
- Encoder mode
- Active in Stop mode.

3.20.5 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

3.20.6 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

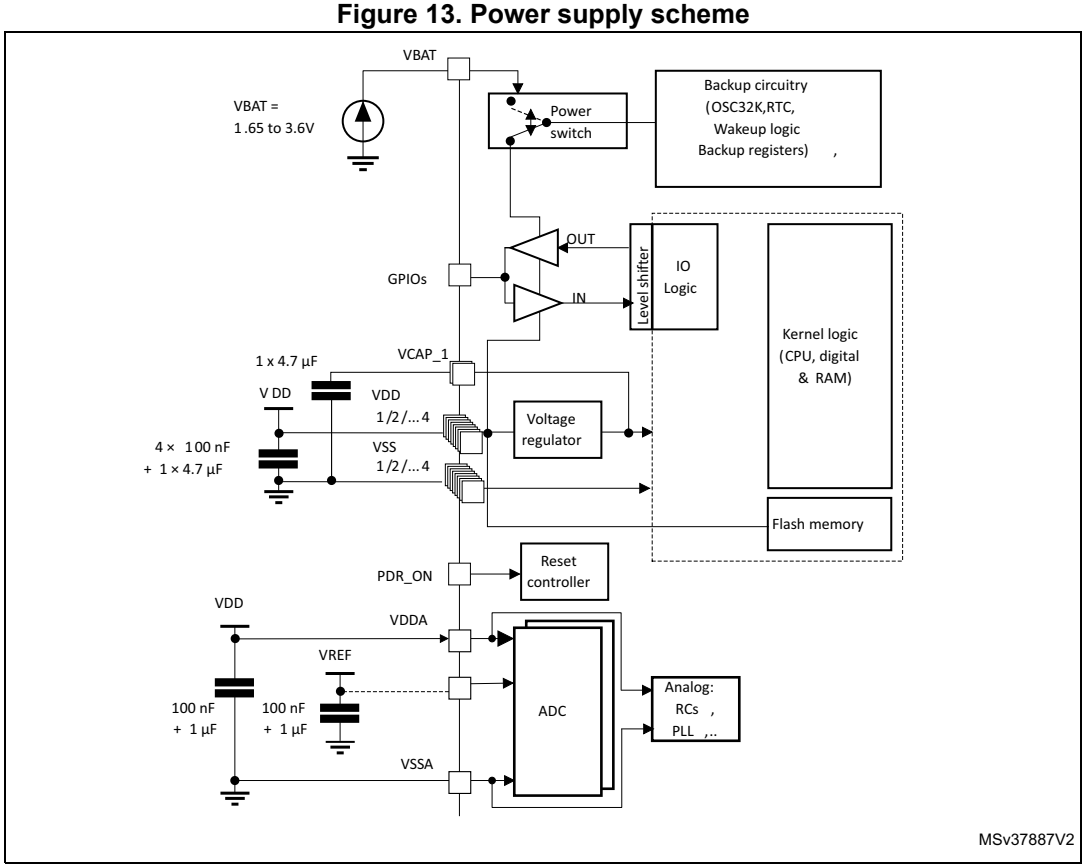
3.20.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

6.1.6 Power supply scheme

Figure 13. Power supply scheme



1. To connect PDR_ON pin, refer to *Section 3.15: Power supply supervisor*.

Caution: Each power supply pair (for example V_{DD}/V_{SS}, V_{DDA}/V_{SSA}) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure good operation of the device. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect operation of the device.

Table 23. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory- V_{DD} = 1.7 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Voltage scale	PLL VCO (MHz) (1)	Typ	Max(2)				Unit
						T_A= 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(3)(4)	100	S1	200	15.7	16.5	16.5	16.9	17.8	mA
			84	S2	168	12.7	13.3	13.4	13.8	14.6	
			64	S3	128	8.8	9.3	9.4	9.7	10.6	
			50	S3	100	7.0	7.4	7.5	7.8	8.6	
			25	S3	100	3.9	4.1	4.3	4.7	5.6	
			20	S3	160	3.4	3.6	3.8	4.2	5.1	
		HSI, PLL OFF, all peripherals enabled(3)(4)	16	S3	off	2.4	2.5	2.8	3.2	4.1	
			1	S3	off	0.6	0.7	1.0	1.4	2.3	
		External clock, all peripherals disabled(3)	100	S1	200	10.1	10.7	10.8	11.2	12.0	
			84	S2	168	8.2	8.6	8.7	9.1	10.0	
			64	S3	128	5.7	6.1	6.2	6.6	7.4	
			50	S3	100	4.6	4.9	5.0	5.4	6.3	
			25	S3	100	2.6	2.8	3.0	3.4	4.3	
			20	S3	160	2.4	2.5	2.8	3.1	4.0	
		HSI, PLL OFF, all peripherals disabled(3)	16	S3	off	1.7	1.8	2.1	2.4	3.3	
			1	S3	off	0.6	0.6	1.0	1.4	2.2	

1. Refer to *Table 44* and RM0401 for the possible PLL VCO setting
2. Guaranteed by characterization, unless otherwise specified.
3. When the ADC is ON (ADON bit set in ADC_CR2), an additional power consumption of 1.6 mA must be added.
4. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register)

Table 37. Low-power mode wakeup timings(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{WUSLEEP}$(2)	Wakeup from Sleep mode	-	-	4	6	CPU clock cycles
$t_{WUSLEEPFDSM}$(2)		Flash memory in Deep power down mode	-	-	40,0	µs
t_{WUSTOP}(2)	Wakeup from Stop mode, code execution from Flash memory	Main regulator	-	12.9	15.0	
		Main regulator, Flash memory in Deep power down mode	-	104.9	115.0	
		Regulator in low-power mode(3)	-	20.8	25.0	
		Regulator in low-power mode, Flash memory in Deep power down mode	-	112.9	120.0	
	Wakeup from Stop mode, code execution from RAM	Main regulator, Flash memory in Stop or Deep power down mode	-	4.9	7.0	
		Regulator in low-power mode, Flash memory in Stop or Deep power down mode(3)	-	12.8	20.0	
$t_{WUSTDBY}$(2)(4)	Wakeup from Standby mode	-	-	316.8	350.0	
$t_{WUFLASH}$	Wakeup of Flash memory	From Flash_Stop mode	-	-	10.0	
	Wakeup of Flash memory	From Flash Deep power down mode	-	-	40.0	

1. Guaranteed by characterization.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. The specification is valid for wakeup from regulator in low power mode or in low power low voltage mode, since the timing difference is negligible.
4. $t_{WUSTDBY}$ maximum value is given at - 40 °C.

6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the *Table 55*. However, the recommended clock input waveform is shown in *Figure 19*.

The characteristics given in *Table 38* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 15*.

Table 40. HSE 4-26 MHz oscillator characteristics(1)

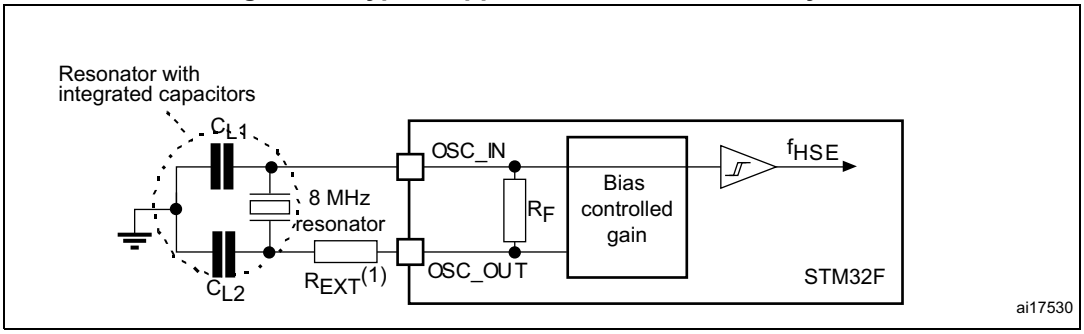
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	V_{DD}=3.3 V, ESR= 30 Ω, C_L=5 pF @25 MHz	-	450	-	µA
		V_{DD}=3.3 V, ESR= 30 Ω, C_L=10 pF @25 MHz	-	530	-	
$G_{m\_crit\_max}$	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}$(2)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 21*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 21. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 41*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 44. Main PLL characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{LOCK}	PLL lock time	VCO freq = 100 MHz		75	-	200	µs
		VCO freq = 432 MHz		100	-	300	
Jitter(3)	Cycle-to-cycle jitter	System clock 100 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	
$I_{DD(PLL)}$(4)	PLL power consumption on VDD	VCO freq = 100 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLL)}$(4)	PLL power consumption on VDDA	VCO freq = 100 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design.
3. The use of two PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization.

Figure 25 and *Figure 26* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 25. PLL output clock waveforms in center spread mode

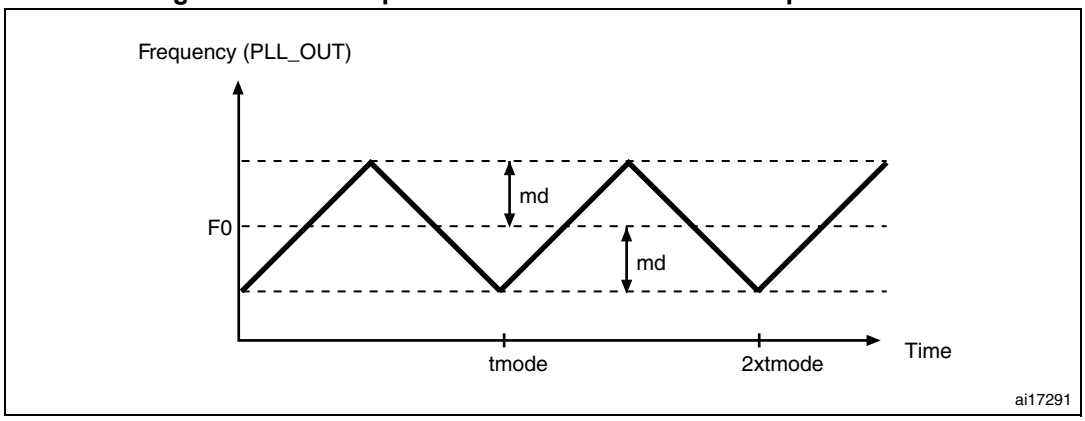
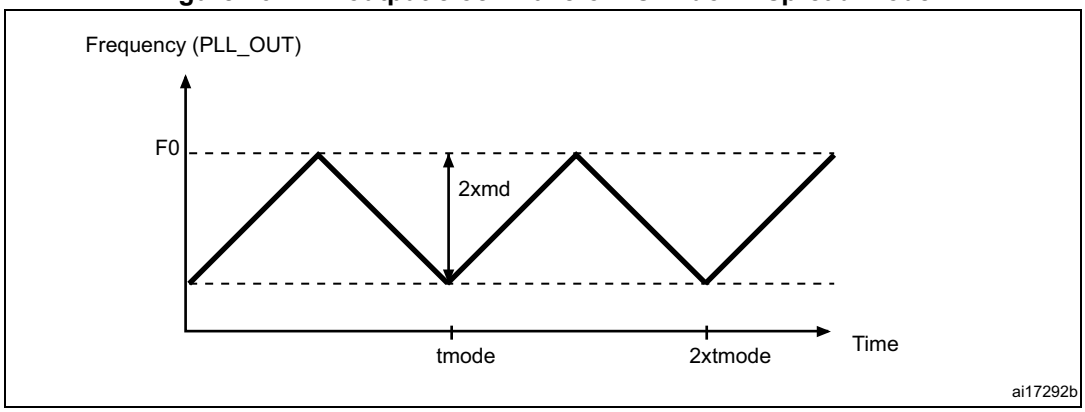


Figure 26. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 125 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

In noisy environments, it is recommended to avoid pin exposition to disturbances. The pins showing a middle range robustness are PA14 and PA15.

As a consequence, it is recommended to add a serial resistor (1 kΩ maximum) located as close as possible to the MCU pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 51. EMI characteristics for LQFP64

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Unit
				8/100 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, conforming to IEC61967-2	0.1 to 30 MHz	10	dBµV
			30 to 130 MHz	11	
			130 MHz to 1 GHz	5	
			SAE EMI Level	2.5	-

6.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 52. ESD absolute maximum ratings(1)

Symbol	Ratings	Conditions		Class	Maximum value(2)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to ANSI/JEDEC JS-001		2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to ANSI/ESD STM5.3.1	UFQFPN48	4	500	
			WLCSP36	3	250	
			LQFP48	4	500	
			LQPF64	4	500	
			UFBGA64	TBD	TBD	

1. TBD stands for “to be defined”.
2. Guaranteed by characterization.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 53. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +125 °C conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Table 55. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
V_{IH}	FT, TC and NRST I/O input high level voltage(5)		1.7 V≤V_{DD}≤3.6 V	0.7V_{DD}(1)	-	-	V
	BOOT0 I/O input high level voltage		1.75 V≤V_{DD} ≤3.6 V, -40 °C≤T_A ≤ 125 °C	0.17V_{DD}+ 0.7(2)	-	-	
			1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤ 125 °C				
V_{HYS}	FT, TC and NRST I/O input hysteresis		1.7 V≤V_{DD}≤3.6 V	-	10% V_{DD}(3)	-	V
	BOOT0 I/O input hysteresis		1.75 V≤V_{DD} ≤3.6 V, - 40 °C≤T_A ≤ 125 °C	-	100	-	mV
			1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤ 125 °C				
I_{lkg}	I/O input leakage current (4)		V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT/TC input leakage current (5)		V_{IN} = 5 V	-	-	3	
R_{PU}	Weak pull-up equivalent resistor(6)	All pins except for PA10 (OTG_FS_ID)	V_{IN} = V_{SS}	30	40	50	kΩ
		PA10 (OTG_FS_ID)	-	7	10	14	
R_{PD}	Weak pull-down equivalent resistor(7)	All pins except for PA10 (OTG_FS_ID)	V_{IN} = V_{DD}	30	40	50	
		PA10 (OTG_FS_ID)	-	7	10	14	
C_{IO}(8)	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by tests in production.
2. Guaranteed by design.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to *Table 54: I/O current injection susceptibility*
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to *Table 54: I/O current injection susceptibility*
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT and TC I/Os is shown in *Figure 27*.

I²S interface characteristics

Unless otherwise specified, the parameters given in *Table 65* for the I²S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 15*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 65. I²S dynamic characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256x8K	256xFs(2)	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	0	7	ns
$t_{h(WS)}$	WS hold time	Master mode	1.5	-	
$t_{su(WS)}$	WS setup time	Slave mode	1.5	-	
$t_{h(WS)}$	WS hold time	Slave mode	3	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	1	-	
$t_{su(SD\_SR)}$		Slave receiver	2.5	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	7	-	
$t_{h(SD\_SR)}$		Slave receiver	2.5	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	20	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	6	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	8	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	2	-	

1. Guaranteed by characterization.
2. The maximum value of 256xFs is 50 MHz (APB1 maximum frequency).

Note: Refer to the I2S section of RM0401 reference manual for more details on the sampling frequency (F_S).

*f_{MCK}, f_{CK}, and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). F_S maximum value is supported for each mode/condition.*

Table 66. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_S(2)	Sampling rate (f_{ADC} = 30 MHz, and t_S = 3 ADC cycles)	12-bit resolution Single ADC	-	-	2	Msps
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msps
I_{VREF+}(2)	ADC V_{REF} DC current consumption in conversion mode	-	-	300	500	µA
I_{VDDA}(2)	ADC V_{DDA} DC current consumption in conversion mode	-	-	1.6	1.8	mA

1. V_{DDA} minimum value of 1.7 V is possible with the use of an external power supply supervisor (refer to *Section 3.15.2: Internal reset OFF*).
2. Guaranteed by characterization.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}.
4. R_{ADC} maximum value is given for V_{DD}=1.7 V, and minimum value for V_{DD}=3.3 V.
5. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 66*.

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 67. ADC accuracy at f_{ADC} = 18 MHz(1)

Symbol	Parameter	Test conditions	Typ	Max(2)	Unit
ET	Total unadjusted error	f_{ADC} =18 MHz V_{DDA} = 1.7 to 3.6 V V_{REF} = 1.7 to 3.6 V V_{DDA} –V_{REF} < 1.2 V	±3	±4	LSB
EO	Offset error		±2	±3	
EG	Gain error		±1	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±2	±3	

1. Better performance could be achieved in restricted V_{DD}, frequency and temperature ranges.
2. Guaranteed by characterization.

Table 68. ADC accuracy at f_{ADC} = 30 MHz(1)

Symbol	Parameter	Test conditions	Typ	Max(2)	Unit
ET	Total unadjusted error	f_{ADC} = 30 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 to 3.6 V, V_{REF} = 1.7 to 3.6 V, $V_{DDA} - V_{REF}$ < 1.2 V	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±4	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. Better performance could be achieved in restricted V_{DD}, frequency and temperature ranges.
2. Guaranteed by characterization.

Table 69. ADC accuracy at f_{ADC} = 36 MHz(1)

Symbol	Parameter	Test conditions	Typ	Max(2)	Unit
ET	Total unadjusted error	f_{ADC} =36 MHz, V_{DDA} = 2.4 to 3.6 V, V_{REF} = 1.7 to 3.6 V $V_{DDA} - V_{REF}$ < 1.2 V	±4	±7	LSB
EO	Offset error		±2	±3	
EG	Gain error		±3	±6	
ED	Differential linearity error		±2	±3	
EL	Integral linearity error		±3	±6	

1. Better performance could be achieved in restricted V_{DD}, frequency and temperature ranges.
2. Guaranteed by characterization.

Table 70. ADC dynamic accuracy at f_{ADC} = 18 MHz - limited test conditions(1)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	f_{ADC} =18 MHz $V_{DDA} = V_{REF+}$= 1.7 V Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		-	-72	-67	

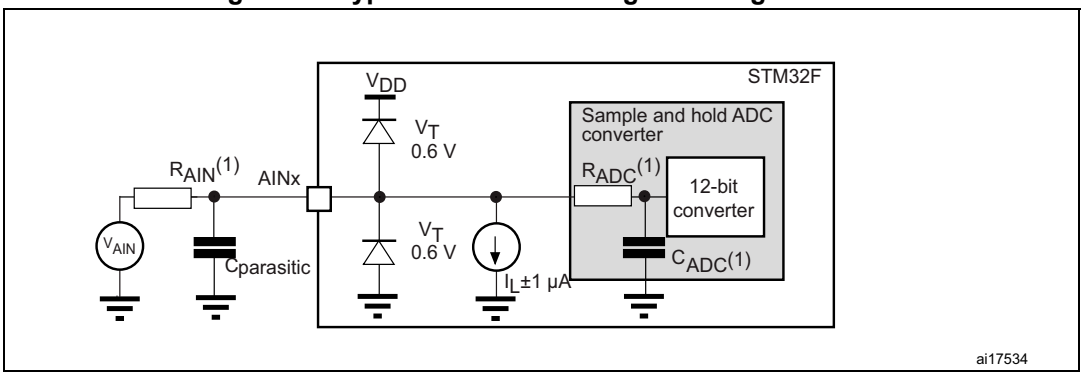
1. Guaranteed by characterization.

Table 71. ADC dynamic accuracy at f_{ADC} = 36 MHz - limited test conditions(1)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	f_{ADC} = 36 MHz $V_{DDA} = V_{REF+}$ = 3.3 V Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		-	-72	-70	

1. Guaranteed by characterization.

Figure 38. Typical connection diagram using the ADC



1. Refer to *Table 66* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

6.3.24 DAC electrical characteristics

Table 77. DAC characteristics

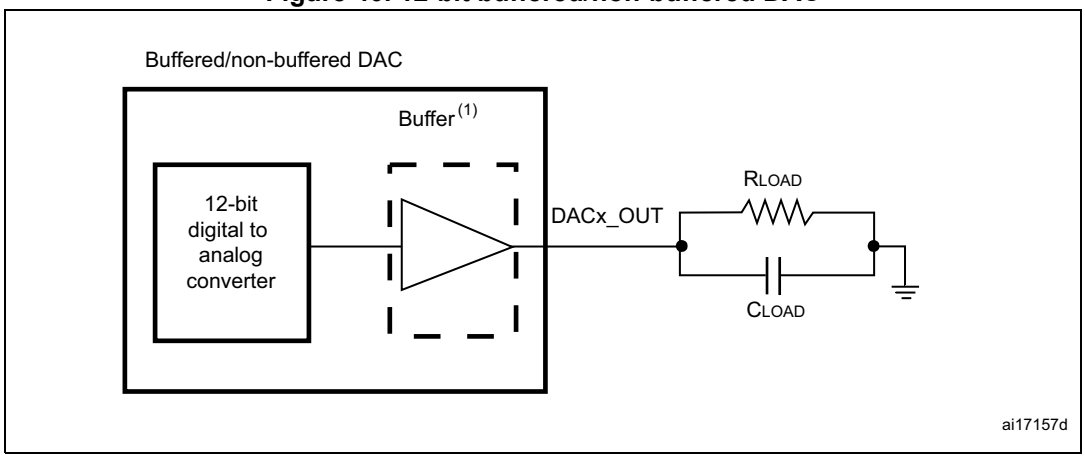
Symbol	Parameter	Conditions		Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	-		1.7(1)	-	3.6	V	-
V_{REF+}	Reference supply voltage	-		1.7(1)	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V_{SSA}	Ground	-		0	-	0	V	-
R_{LOAD}(2)	Resistive load	DAC output buffer ON	R_{LOAD} connected to V_{SSA}	5	-	-	kΩ	-
			R_{LOAD} connected to V_{DDA}	25	-	-	kΩ	-
R_O(2)	Impedance output with buffer OFF	-		-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(2)	Capacitive load	-		-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer ON	-		0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x1C7) to (0xE38) at V_{REF+} = 1.7 V
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer ON	-		-	-	V_{DDA} – 0.2	V	
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer OFF	-		-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer OFF	-		-	-	V_{REF+} – 1LSB	V	
I_{VREF+}(4)	DAC DC V_{REF} current consumption in quiescent mode (Standby mode)	-		-	170	240	µA	With no load, worst code (0x800) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
		-		-	50	75		With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs

Table 77. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	Comments
t_{WAKEUP}(4)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (2)	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	-	- –67	- 40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 3.15.2: Internal reset OFF*).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed based on test during characterization.

Figure 40. 12-bit buffered/non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

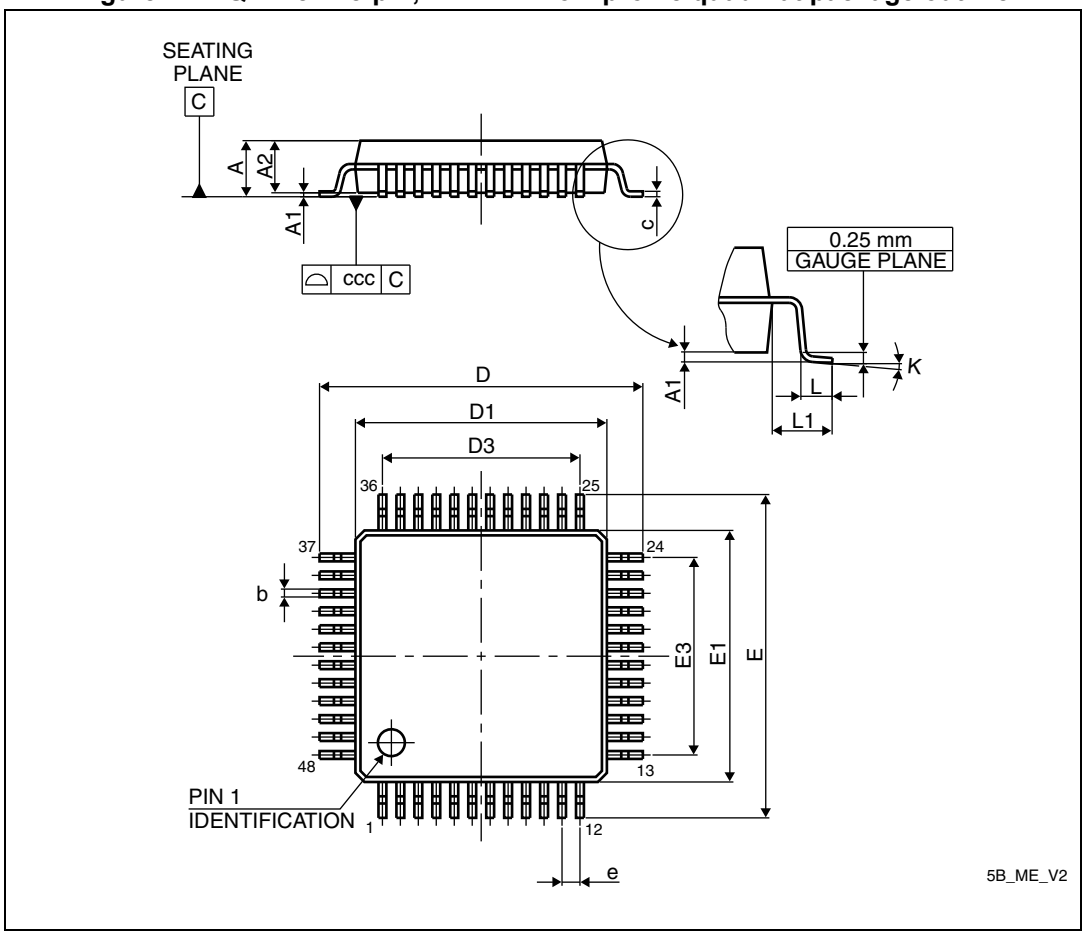
6.3.25 RTC characteristics

Table 78. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

7.3 LQFP48 package information

Figure 47. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



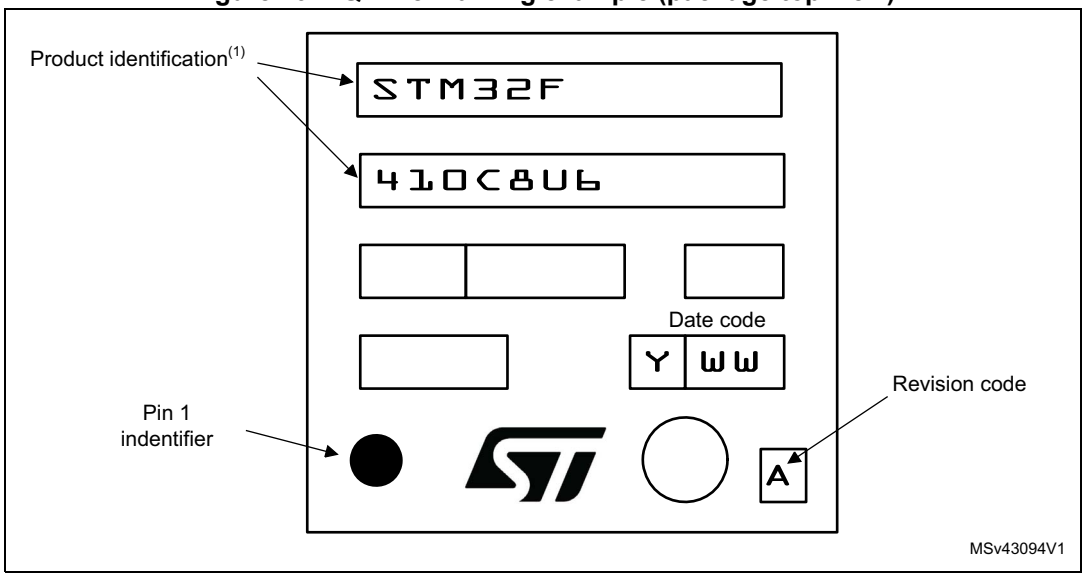
1. Drawing is not to scale.

LQFP48 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 49. LQFP48 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.